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SPC-F005.DWG

REVISIONS

DOC. NO. SPC-F005 * Effective: 7/8/02 * DCP No: 1398

DCP #	REV	DESCRIPTION	DRAWN	DATE	CHECKD	DATE	APPRVD	DATE
2048	A	RELEASED	JN	05/21/09	JWM	05/21/09	JWM	05/21/09

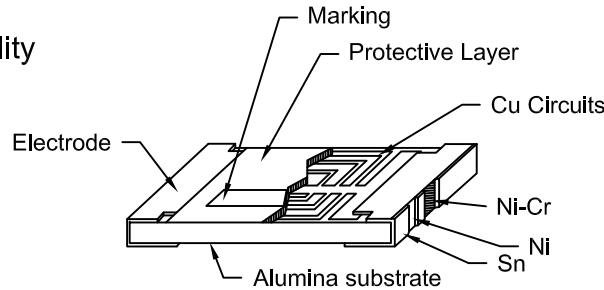
Features

- Photolithographic single layer ceramic chip
- High SRF, excellent Q, superior temperature stability
- Tight tolerance of $\pm 1\%$ or $\pm 0.1nH$
- Self resonant frequency controlled within 10%
- Stable inductance in high frequency circuit
- Highly stable design for critical needs

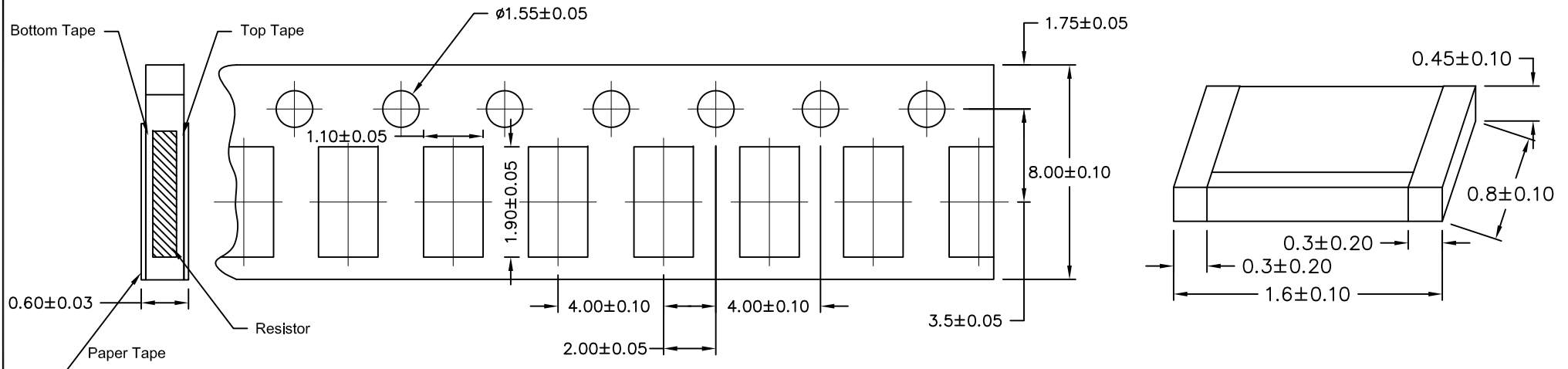


Application

- Cellular Phone, Pagers and GPS Products
- VCO, TCXO, Circuit an dRF Transceiver Module
- Wireless LAN Bluetooth module, Communication Appliances



Tape Dimension



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TOLERANCES:
UNLESS OTHERWISE SPECIFIED, DIMENSIONS ARE FOR REFERENCE PURPOSES ONLY.

DRAWN BY:	DATE:
Jason Nash	05/21/09
CHECKED BY:	DATE:
JWM	05/21/09
APPROVED BY:	DATE:
JWM	05/21/09

DRAWING TITLE: Thin Film Chip Inductor – Case size 0603			
SIZE	DWG. NO.	ELECTRONIC FILE	REV
A	Ta-1128	Ta-1128.DWG	A
SCALE:	U.O.M.:	SHEET:	
NTS	Millimeters	1 OF 2	

Item	Specification	Test Method
1 Bending Test	As SPEC.	JIS-C-5202-6.1.4 Bending Amplitude 3mm for 10 seconds
2 Dielectric Withstand Voltage	>100V	MIL-STD-202F Method 301. Apply 100VA (rms) for 1minute.
3 Insulation Resistance	>1000MΩ	MIL-STD-202F Method 302 Apply 100VDC for 1minute.
4 Resistance to Soldering Heat	ΔL<10%	MIL-STD-202F Method 210E 260±5°C, 10±1seconds
5 High Temperature Exposure	ΔL<10%	JIS-C-5202-7.2 85±2°C, 1000 +48/-0 hours
6 Moisture Resistance	ΔL<10%	MIL-STD-202F Method 103B 40±2°C, 90~95%RH, 1000 +48/-0 hours
7 Low Temperature Storage	ΔL<10%	JIS-C-5202-7.1 -40±3°C, 1000 +48/-0 hours
8 Temperature Cycle	ΔL<10%	JIS-C-5202-7.4 -40/RT/85/RT, 10 cycles
9 Solderability	95% min coverage	MIL-STD-202F Method 208H 245°C ±5°C, 3±0.5(sec)

Mfr PN	Inductance	Inductance Tolerance	DC Resistance Max	DC Current Rating	Self Resonant Frequency	Package/ Case	Q Factor	Test Frequency
MCFT000011	1nH	±0.1 nH	0.35ohm	800mA	13GHz	603	Q Factor:15	300MHz
MCFT000012	1.5nH	±0.1 nH	0.35ohm	800mA	10GHz	603	Q Factor:15	300MHz
MCFT000013	2.2nH	±0.1 nH	0.35ohm	300mA	8GHz	603	Q Factor:15	300MHz
MCFT000014	3.3nH	±0.1 nH	0.45ohm	300mA	6GHz	603	Q Factor:15	300MHz
MCFT000015	4.7nH	±0.1 nH	0.55ohm	300mA	5GHz	603	Q Factor:15	300MHz
MCFT000016	6.8nH	±0.1 nH	0.75ohm	300mA	5GHz	603	Q Factor:15	300MHz
MCFT000017	10nH	±1%	0.95ohm	300mA	4GHz	603	Q Factor:15	300MHz
MCFT000018	15nH	±1%	1.35ohm	300mA	3GHz	603	Q Factor:15	300MHz
MCFT000019	22nH	±1%	1.95ohm	250mA	2GHz	603	Q Factor:15	300MHz
MCFT000020	33nH	±1%	2.75ohm	250mA	1.5GHz	603	Q Factor:15	300MHz
MCFT000021	47nH	±1%	3ohm	200mA	1.5GHz	603	Q Factor:15	300MHz
MCFT000022	68nH	±1%	5ohm	150mA	1GHz	603	Q Factor:15	300MHz
MCFT000023	100nH	± 2%	7.5ohm	100mA	1GHz	603	Q Factor:15	300MHz

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SIZE DWG. NO.

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Ta-1128

ELECTRONIC FILE

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REV

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